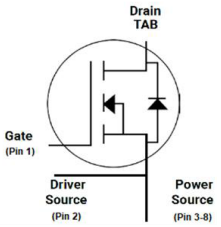
DAC036N065LY3

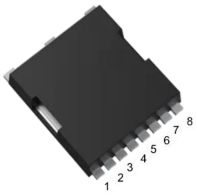
Silicon Carbide Enhancement Mode MOSFET

V_{DSS}	650V
$I_{D(@25℃)}$	65A
$R_{DS(ON)}$ typ.	36mΩ

Features

- High blocking voltage with low Rds(on)
- High frequency operation with low Capacitance
- Simple to drive with -4V/+18V gate
- Robust body diode with low Qrr
- 100% Avalanche tested





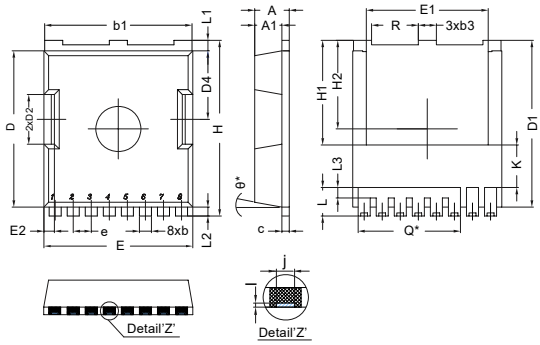
Benefits

- Superior robustness and system reliability
- Higher system efficiency
- Easier paralleling without thermal runaway
- Capable of high temperature application
- Faster and more efficient switching

Applications

- Server power
- EV/HEV charging station
- Energy storage systems
- High performance DC-DC converters
- On-board charger
- Battery management systems

Package Dimensions



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b3	1.10	1.20	1.30
c	0.40	0.50	0.60
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D4	4.45	4.55	4.65
E	9.80	9.90	10.00
E1	8.00	8.10	8.20
E2	0.60	0.70	0.80
e	1.20 BSC		
H	11.58	11.68	11.78
H1	6.95 BSC		
H2	5.89 BSC		
I	0.10 REF.		
j	0.46 REF.		
K	2.80 REF.		
L	1.40	1.90	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.30	0.70	0.80
N	8		
Q	6.80 REF.		
R	3.00	3.10	3.20
θ	10° REF.		

NOTE:
1. REFER TO JEDEC MO-299B.
2. All DIMENSIONS ARE IN MM, ANGLES IN DEGREES.
3. DIMENSIONS DO NOT INCLUSIVE BURRS AND MOLD FLASH.
4. "*" IS FOR REFERENCE.

Absolute Maximum Ratings

(Tc = 25℃ unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage	V_{GS}=0V I_D=100μA	V_{DS}	650	V
Gate-Source Voltage (dynamic)	AC (f>1 Hz, duty cycle<1%, pulse width<200ns)	V_{GS}	-9/+23	V
Gate-Source Voltage (static)		$V_{GS(op)}$	-4/+18	V
Drain Current-Continuous	@ T_C=25°C @ T_C=100°C	I_D	65 45	A
Pulse Drain Current		$I_{D,pulse}$	155	A
Power Dissipation		P_D	200	W
Storage Temperature Range		T_{STG}	-55 to +175	°C
Operating Junction Temperature Range		T_J	-55 to +175	°C
Soldering Temperature		T_L	260	°C
Avalanche Capability, single pulse *	V_{DD}=100V V_{GS}=10V L=2mH	I_{AV}	27	A
Avalanche Capability, single pulse**	V_{DD}=100V V_{GS}=10V L=2mH	E_{AV}	690	mJ

* 100% tested in 60% rating
** 100% tested in 36% rating

Electrical Characteristics @ T_C =25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V，I_D =0.1mA	650	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =650V，V_{GS} =0V	-	0.5	60	μA
		V_{DS} =650V，V_{GS} =0V，T_J =175°C	-	5	200	
Gate-Source Leakage Current	I_{GSS}	V_{GS} =18V，V_{DS} =0V	-	5	100	nA
		V_{GS} =-4V，V_{DS} =0V	-100	-5	-	
ON Characteristics						
Gate Threshold Voltage **	$V_{GS(th)}$	V_{DS} = V_{GS}，I_D =6mA	2.3	2.9	3.8	V
		V_{DS} = V_{GS}，I_D =6mA ，T_J =150°C	-	2.2	-	
		V_{DS} = V_{GS}，I_D =6mA ，T_J =175°C	-	2.1	-	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} =18V，I_D =20A	-	36	45	mΩ
		V_{GS} =18V，I_D =20A，T_J =175°C	-	44	-	
Transconductance	g_{fs}	V_{DS} =20V，I_D =20A	-	19	-	S
		V_{DS} =20V，I_D =20A，T_J =175°C	-	17	-	
Internal Gate Resistance	$R_{G(int.)}$	f =1MHz，I_D =0A	-	1.0	-	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} =400V V_{GS} =0V Freq.=1MHz V_{AC} =25mV	-	1280	-	pF
Output Capacitance	C_{oss}		-	110	-	
Reverse Transfer Capacitance	C_{rss}		-	8	-	
C oss Stored Energy	E_{oss}		-	11	-	μJ
Turn-On Switching Energy	E_{on}	V_{DS} =400V，V_{GS} =-4/+18V I_D =20A，$R_{G(ext)}$ =2.0Ω L=200μH	-	33	-	μJ
Turn-Off Switching Energy	E_{off}		-	4.8	-	
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	V_{DS} =400V，V_{GS} =-4/+18V I_D =20A，$R_{G(ext)}$ =2.0Ω L=200μH	-	7	-	ns
Rise Time	t_r		-	5	-	
Turn-Off Delay Time	$t_{d(off)}$		-	16	-	
Fall Time	t_f		-	6	-	
Total Gate Charge	Q_g	V_{DS} =400V V_{GS} =-4/+18V I_D =20A	-	60	-	nC
Gate to Source Charge	Q_{gs}		-	16	-	
Gate to Drain Charge	Q_{gd}		-	15	-	
Body Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V ，I_{SD}=20A，T_J =25°C	-	3.7	-	V
		V_{GS}=0V ，I_{SD}=20A，T_J =175°C	-	3.3	-	
Continuous Diode Forward Current	I_S	V_{GS}=-4V，T_J =25°C	-	35	-	A
Reverse Recovery Time	T_{rr}	I_{SD}=20A，V_{GS}=-4V V_R=400V L=200μH，dif/dt=2396A/μs	-	15	-	ns
Reverse Recovery Charge	Q_{rr}		-	130	-	nC
Peak Reverse Recovery Current	I_{rrm}		-	21	-	A
Thermal Resistance						
Thermal Resistance, Junction-to-Case	$R\theta_{JC}$		-	0.75	0.90	°C/W

** Turn-off with -4V gate bias is highly recommended

Typical Performance

Fig 1. Output Characteristics, T_J = -40°C

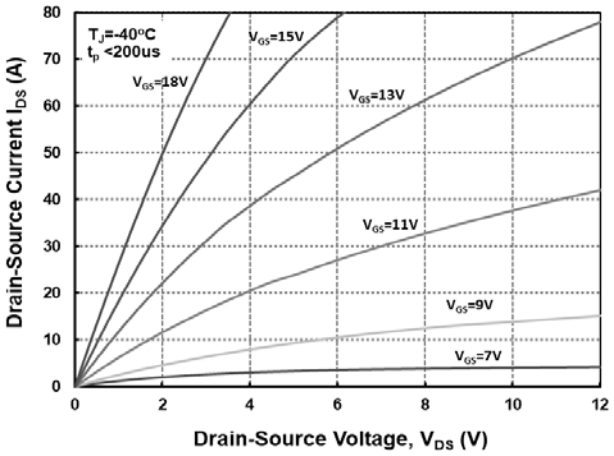


Fig 2. Output Characteristics, T_J = 25°C

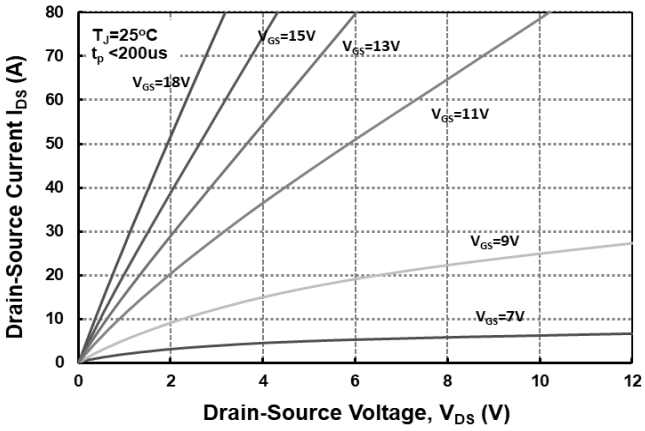


Fig 3. Output Characteristics at T_J =175℃

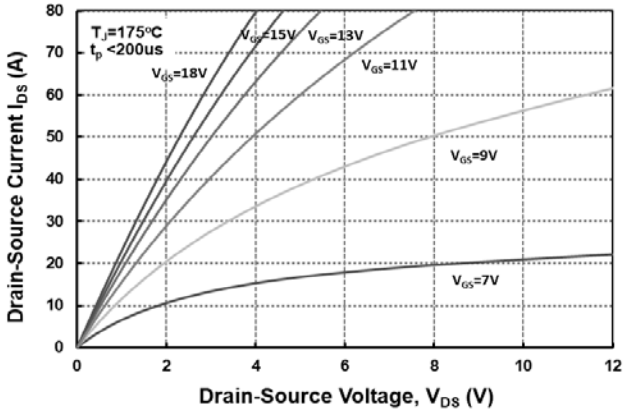


Fig 4. Normalized On-Resistance vs. Temperature

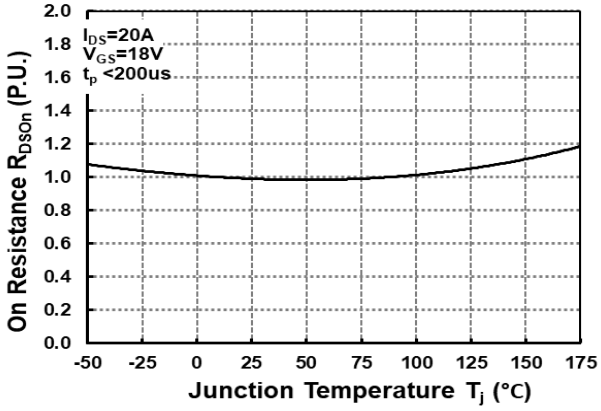


Fig 5. On-Resistance vs. Drain Current for Various Temperatures

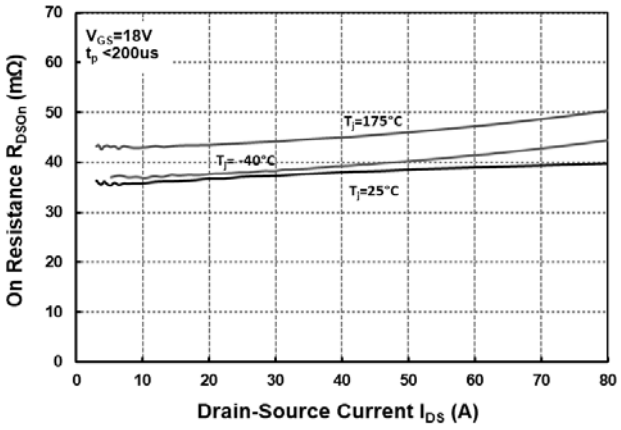
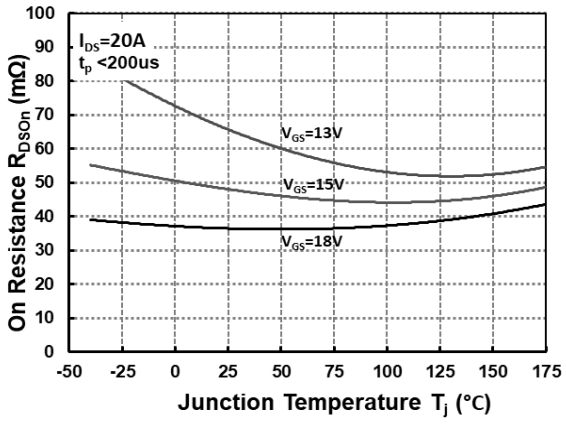


Fig 6. On-Resistance vs. Temperature for Various Gate Voltage



Typical Performance

Fig 7. Transfer Characteristic for Various Junction Temperatures

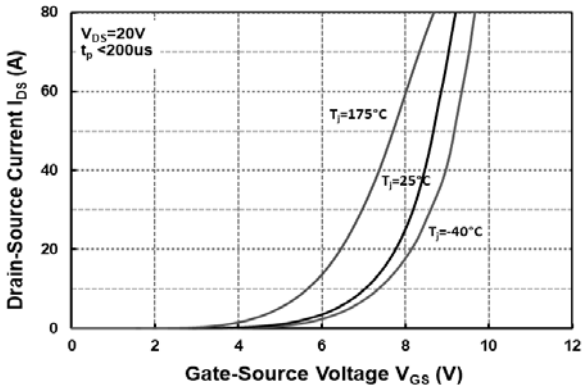


Fig 8. Body Diode Characteristics @ -40°C

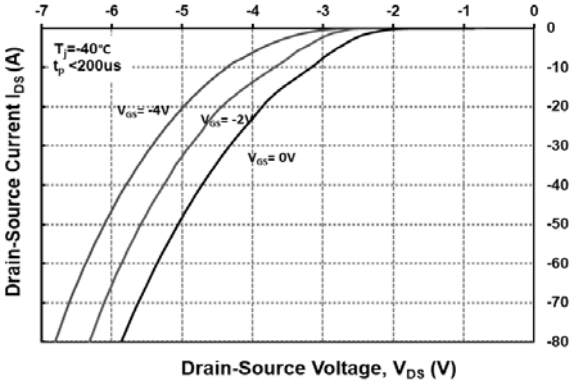


Fig 9. Body Diode Characteristics @ 25°C

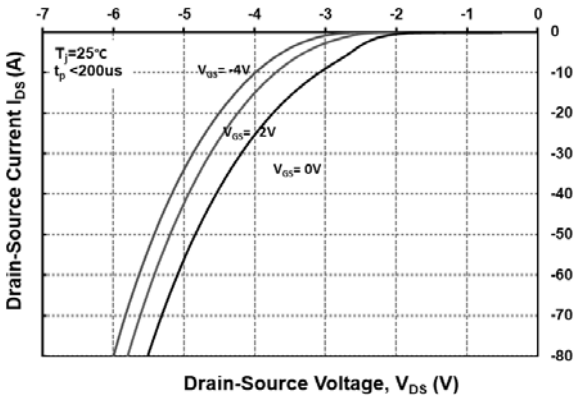


Fig 10. Body Diode Characteristics @ 175°C

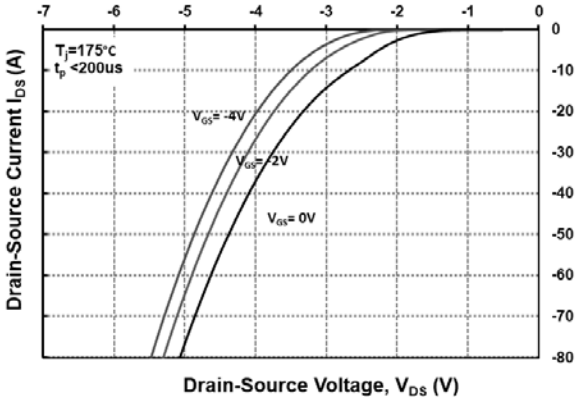


Fig 11. Threshold Voltage vs. Temperature

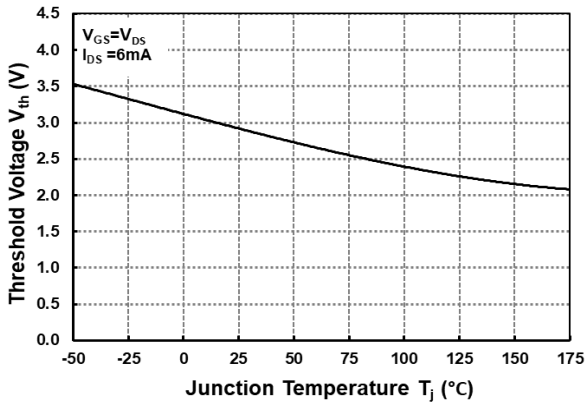
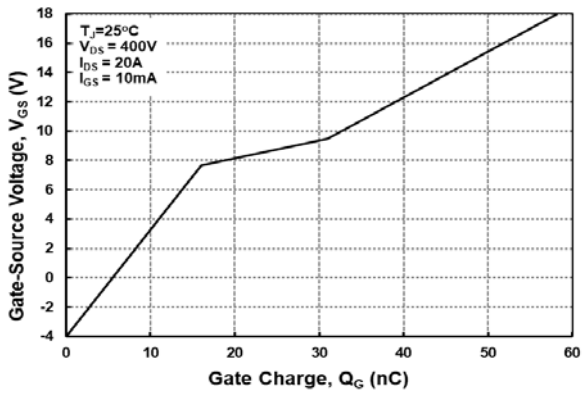


Fig 12. Gate Charge Characteristics



Typical Performance

Fig 13. 3rd Quadrant Characteristics @ -40°C

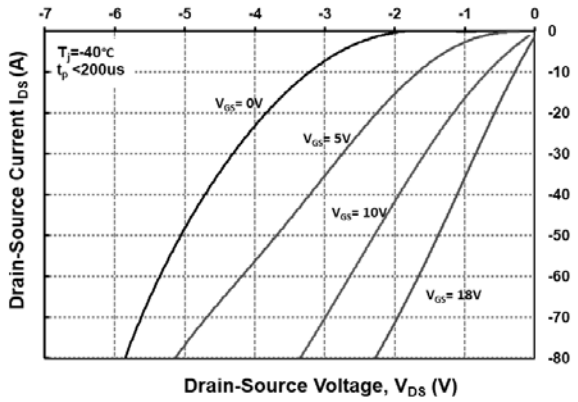


Fig 14. 3rd Quadrant Characteristics @ 25°C

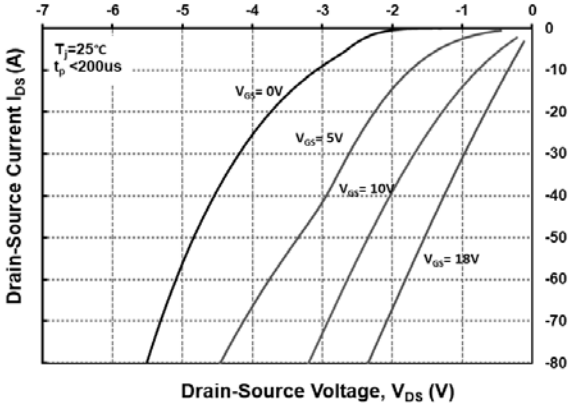


Fig 15. 3rd Quadrant Characteristics @ 175°C

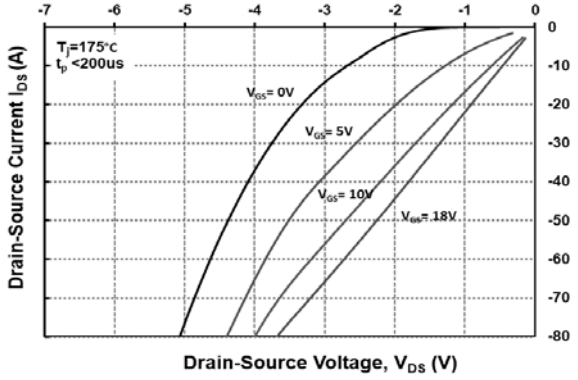


Fig 16. Output Capacitor Stored Energy

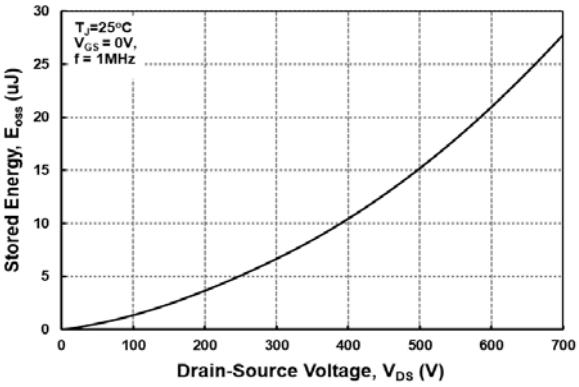


Fig 17. Capacitances vs. Drain-Source Voltage (0-200V)

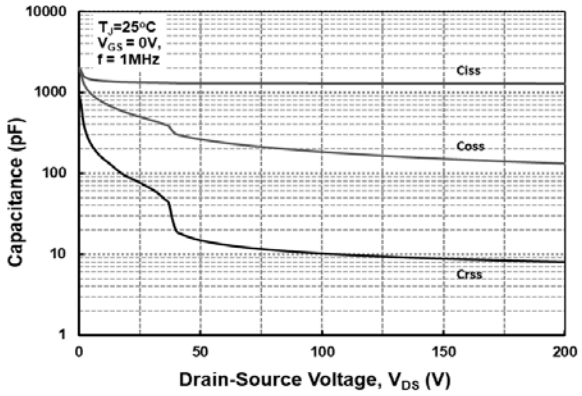
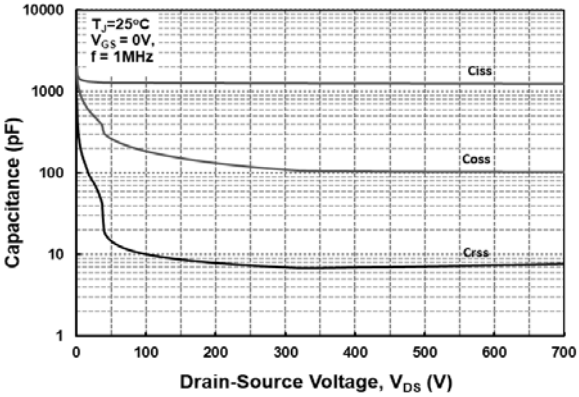


Fig 18. Capacitances vs. Drain-Source Voltage (0-650V)



Typical Performance

Fig 19. Continuous Drain Current Derating vs. Case Temperature

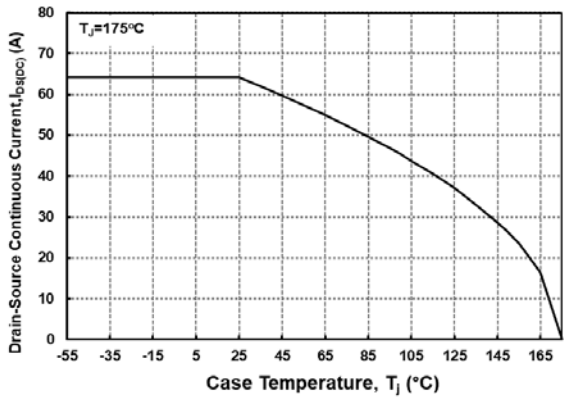


Fig 20. Maximum Power Dissipation Derating vs. Case Temperature

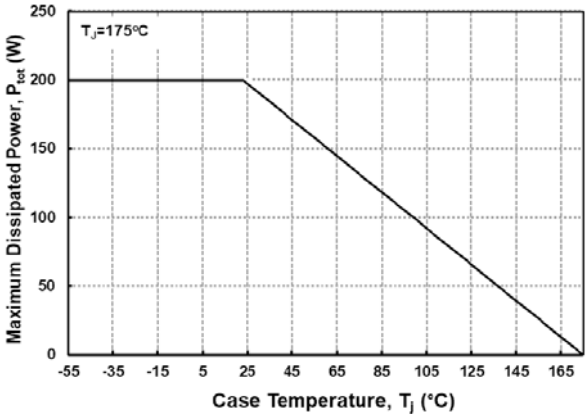


Fig 21. Transient Thermal Impedance (Junction – Case)

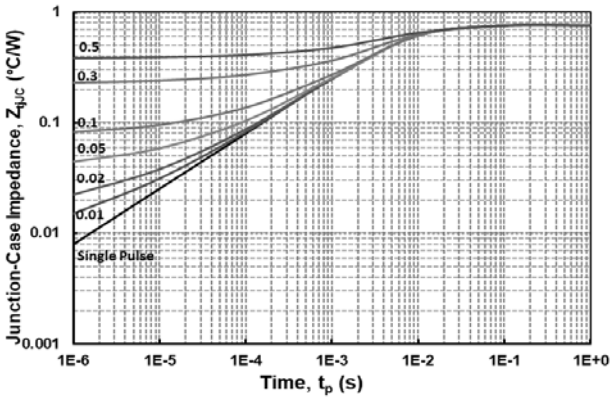


Fig 22. Safe Operating Area

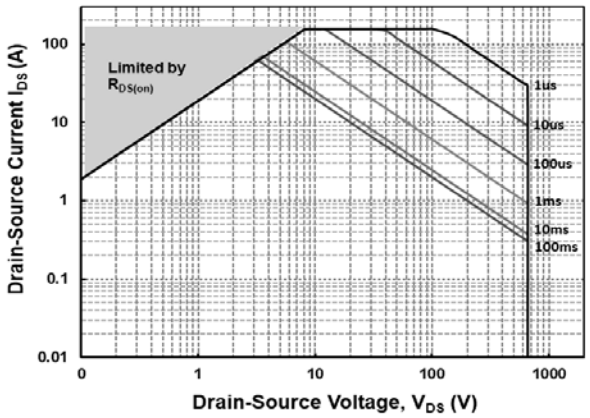


Fig 23. Clamped Inductive Switching Energy vs Drain Current (V_{DD} = 400V)

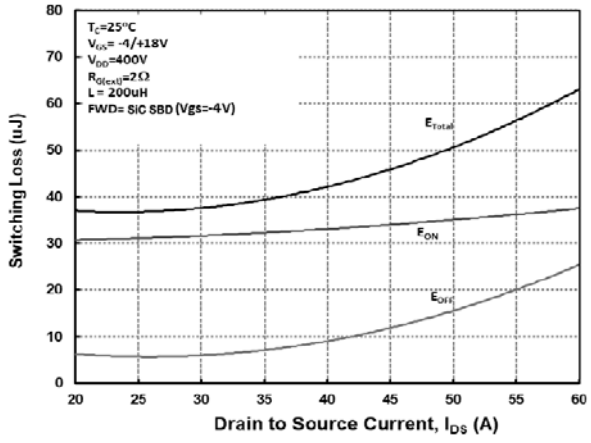
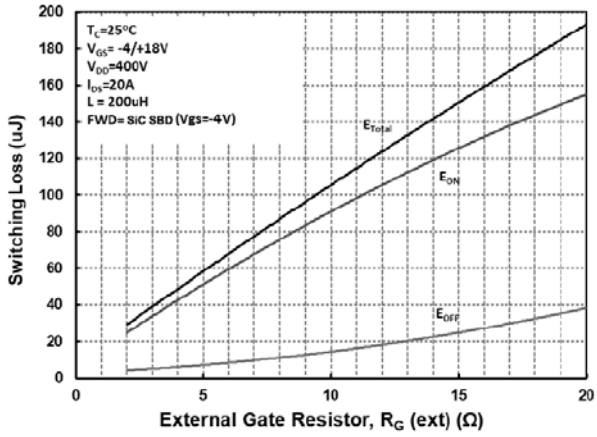


Fig 24. Clamped Inductive Switching Energy vs External Gate Resistor $R_{G(ext)}$



Typical Performance

Fig 25. Switching Times vs Drain Current (V_{DD} = 400V)

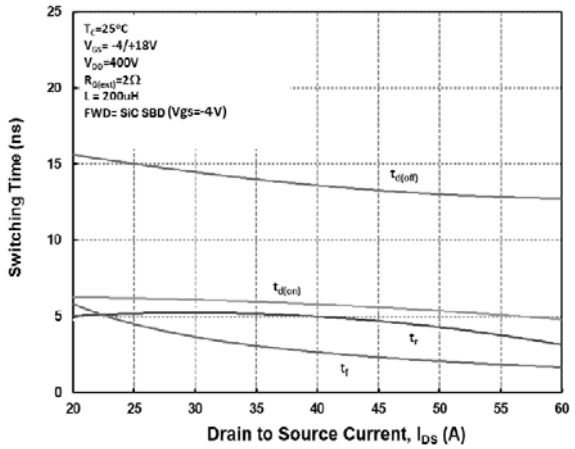
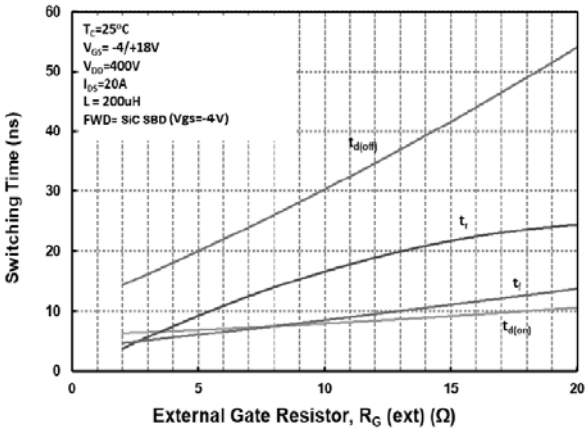


Fig 26. Switching Times vs External Gate Resistor $R_{G(ext)}$



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